

Moon-Kyu Cho

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Design and Analysis of a Low Loss, Wideband Digital Step Attenuator With Minimized Amplitude and Phase Variations. IEEE Journal of Solid-State Circuits, 2018, 53, 2202-2213.	5.4	57
2	An X-Band 5 Bit Phase Shifter With Low Insertion Loss in 0.18 μm SOI Technology. IEEE Microwave and Wireless Components Letters, 2012, 22, 648-650.	3.2	23
3	A Switchless CMOS Bi-Directional Distributed Gain Amplifier With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2013, 23, 611-613.	3.2	23
4	A New Wideband, Low Insertion Loss, High Linearity SiGe RF Switch. IEEE Microwave and Wireless Components Letters, 2020, 30, 985-988.	3.2	23
5	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. IEEE Microwave and Wireless Components Letters, 2016, 26, 595-597.	3.2	19
6	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. IEEE Transactions on Nuclear Science, 2016, 63, 1099-1108.	2.0	13
7	An Active Bi-Directional SiGe DPDT Switch With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 279-281.	3.2	13
8	A SiGe-BiCMOS Wideband Active Bidirectional Digital Step Attenuator With Bandwidth Tuning and Equalization. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 3866-3876.	4.6	13
9	A SiGe-BiCMOS Wideband (22 GHz) Active Power Divider/Combiner Circuit Supporting Bidirectional Operation. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 4676-4684.	4.6	12
10	Compact X-band CMOS bidirectional gain amplifier without T/R switches. Electronics Letters, 2013, 49, 66-68.	1.0	11
11	Encapsulated Organic Package Technology for Wideband Integration of Heterogeneous MMICs. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 438-448.	4.6	11
12	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	2.0	9
13	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	2.0	9
14	Optimization of SiGe HBT RF Switches for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2015, 62, 3057-3063.	2.0	8
15	The Use of Inverse-Mode SiGe HBTs as Active Gain Stages in Low-Noise Amplifiers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 359-366.	2.0	8
16	A Compact, Active SiGe Power Divider With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 945-947.	3.2	6
17	p-n-p-Based RF Switches for the Mitigation of Single-Event Transients in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2018, 65, 391-398.	2.0	6
18	A 28-GHz Switchless, SiGe Bidirectional Amplifier Using Neutralized Common-Emitter Differential Pair. IEEE Microwave and Wireless Components Letters, 2018, 28, 717-719.	3.2	6

#	ARTICLE	IF	CITATIONS
19	Investigation of T -Doubler Technique to Improve RF Performance of Inverse-Mode SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2020, 30, 873-875.	3.2	5
20	Design Methodology for a Wideband, Low Insertion Loss, Digital Step Attenuator in SiGe BiCMOS Technology. IEEE Transactions on Circuits and Systems II: Express Briefs, 2022, 69, 744-748.	3.0	5
21	An Electrostatic Discharge Protection Circuit Technique for the Mitigation of Single-Event Transients in SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 426-431.	2.0	4
22	A multimode phase shifter for S-band phased array antenna. Microwave and Optical Technology Letters, 2018, 60, 1921-1924.	1.4	4
23	Co-design of a SiGe BiCMOS X-band, asymmetric, low insertion loss, high power handling SPDT Switch and an Ultra Low Noise LNA for next-generation T/R modules. , 2016, , .		3
24	Best Practices for Using Electrostatic Discharge Protection Techniques for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2019, 66, 240-247.	2.0	3
25	A Two-Way Wideband Active SiGe BiCMOS Power Divider/Combiner for Reconfigurable Phased Arrays With Controllable Beam Width. IEEE Access, 2020, 8, 2578-2589.	4.2	2
26	A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator A New Wideband, Low Insertion Loss SiGe Digital Step Attenuator. , 2020, , .		2
27	Advantages of utilizing through-silicon vias in SiGe HBT RF low-noise amplifier design. Microwave and Optical Technology Letters, 2015, 57, 2703-2706.	1.4	1
28	Inverse class-F X-band S/G e HBT power amplifier with 44% PAE and 24.5 dBm peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	1.4	1
29	Wideband active bi-directional SiGe digital step attenuator using an active DPDT switch. , 2016, , .		1
30	A 2-20 GHz SiGe Amplitude Control Circuit with Differential Signal Selectivity for Wideband Reconfigurable Electronics. , 2019, , .		1
31	Design of an 18-50 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier. , 2020, , .		1
32	Cryogenic Characterization of RF Low-Noise Amplifiers Utilizing Inverse-Mode SiGe HBTs for Extreme Environment Applications. IEEE Transactions on Device and Materials Reliability, 2018, 18, 613-619.	2.0	0